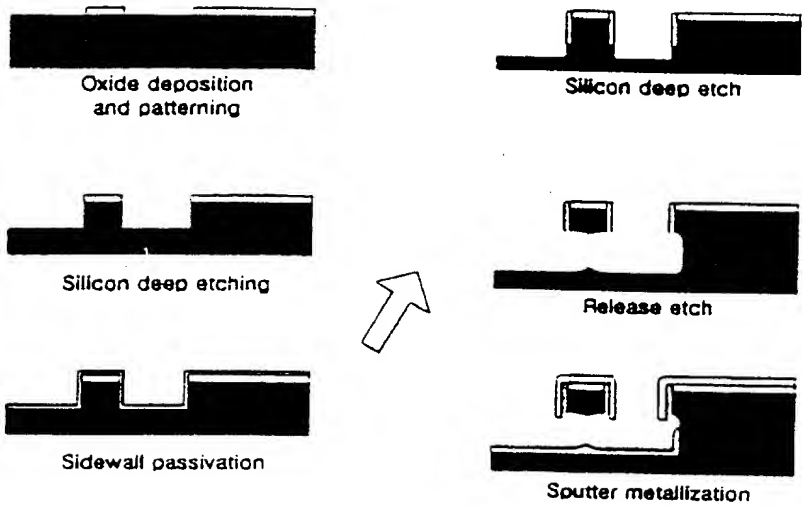


TOP/0"082E0660

FIG. 1



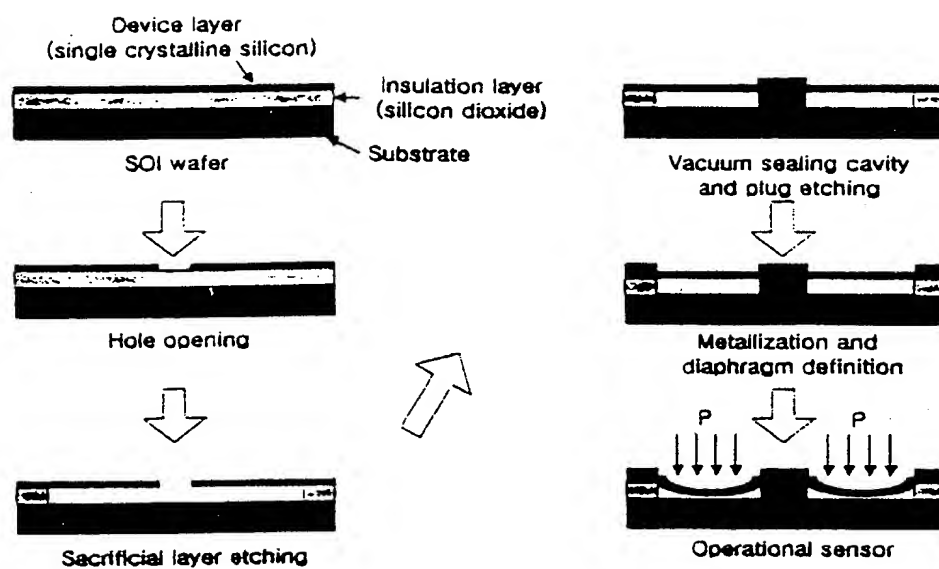
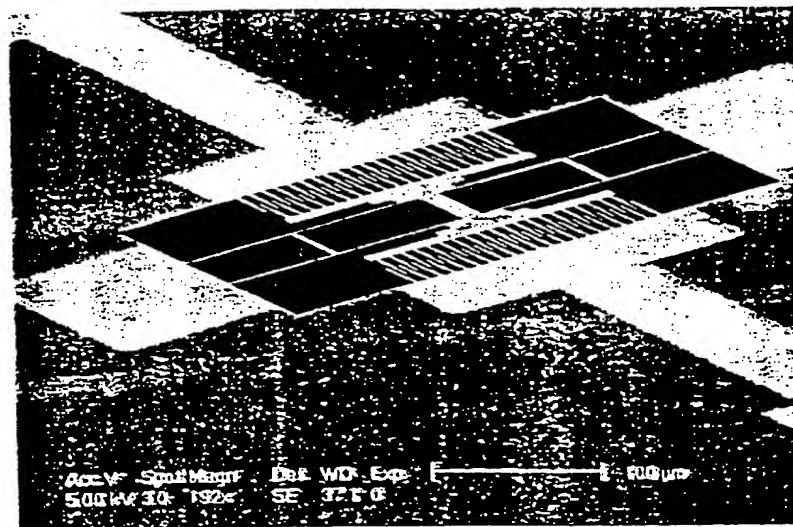
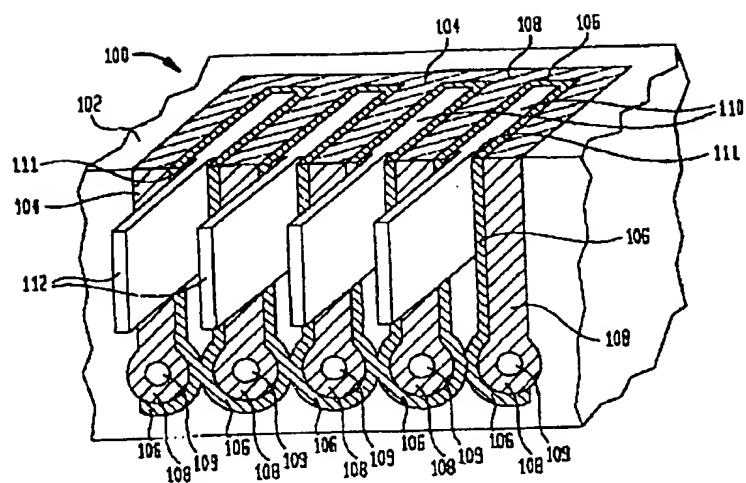
[illegible]

FIG. 3



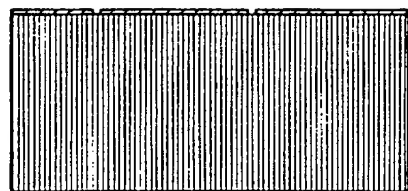
09903380 07101

FIG. 4

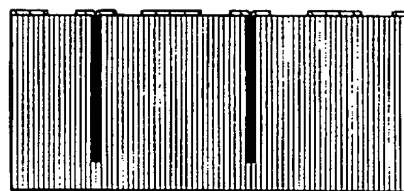


09903280.07301

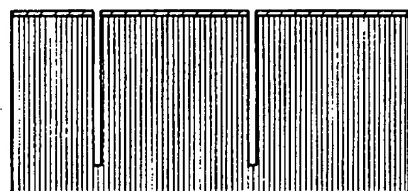
FIG. 5



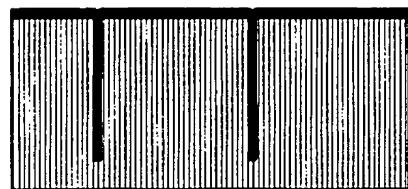
First etch mask deposition and patterning



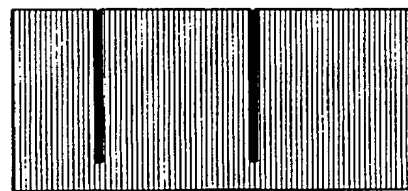
Second etch mask deposition and patterning



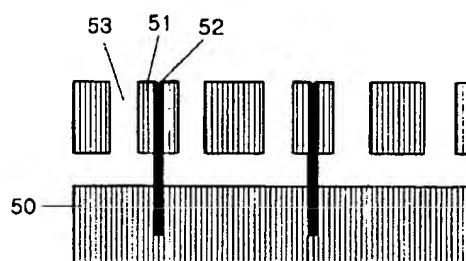
Deep silicon etching to form trenches



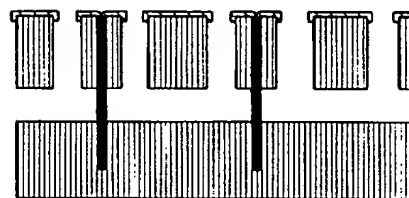
Trench filling by oxidation



Top oxide removal



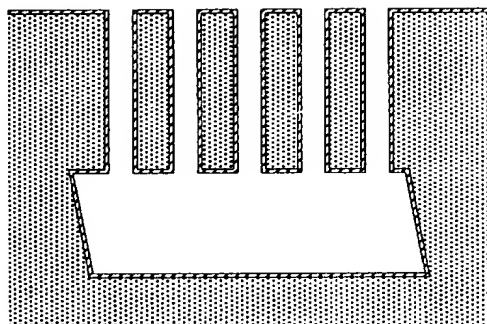
Structure fabrication



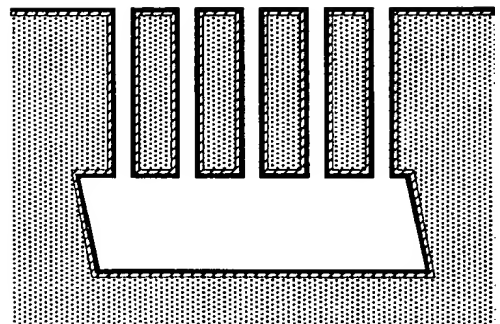
Metallization

09903230.071.01

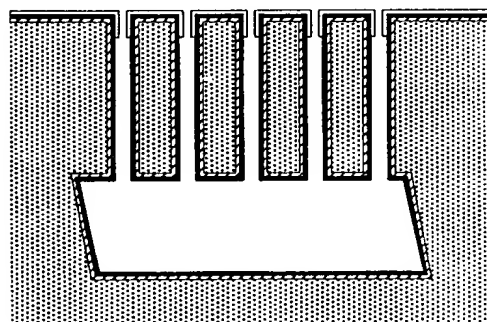
FIG. 6



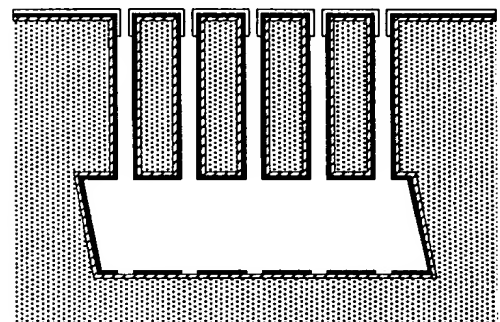
(a)



(b)



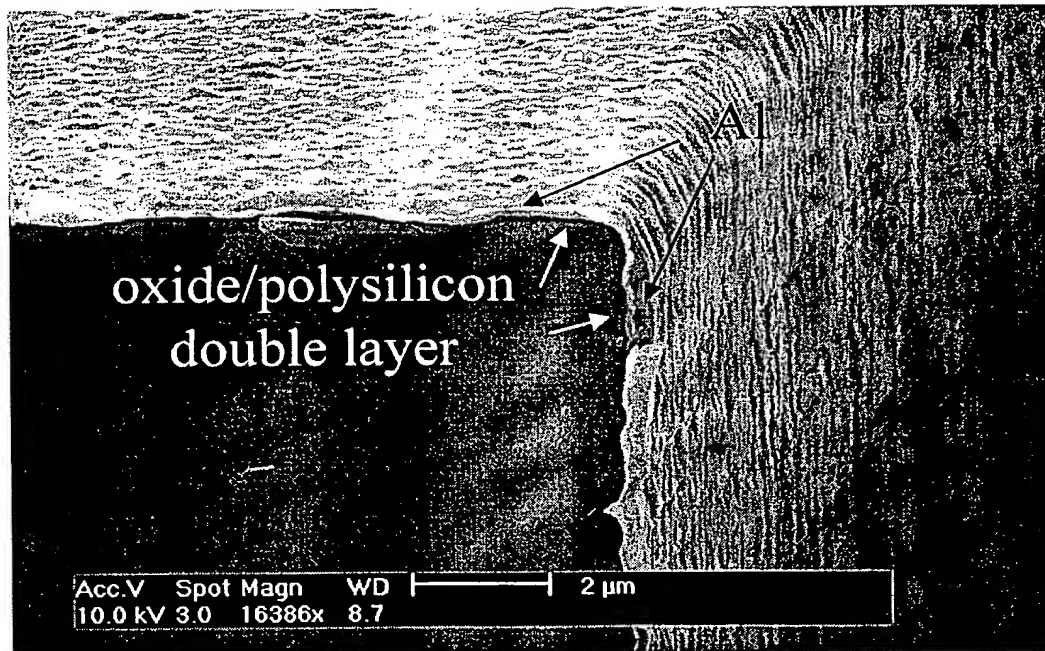
(c)



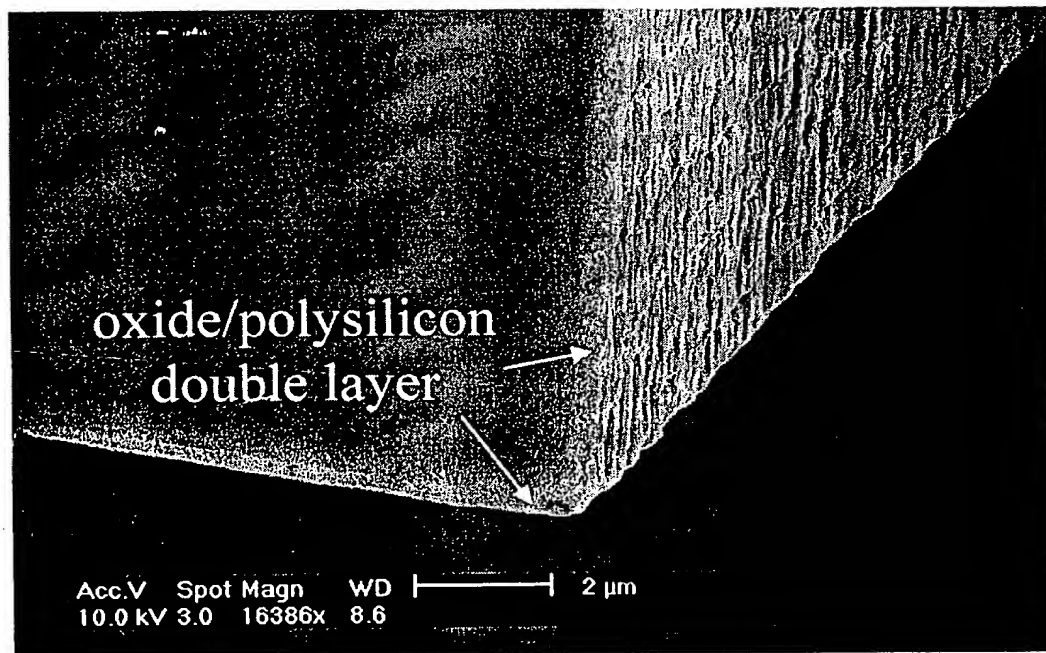
(d)



FIG. 7



(a)



(b)

FIG. 8

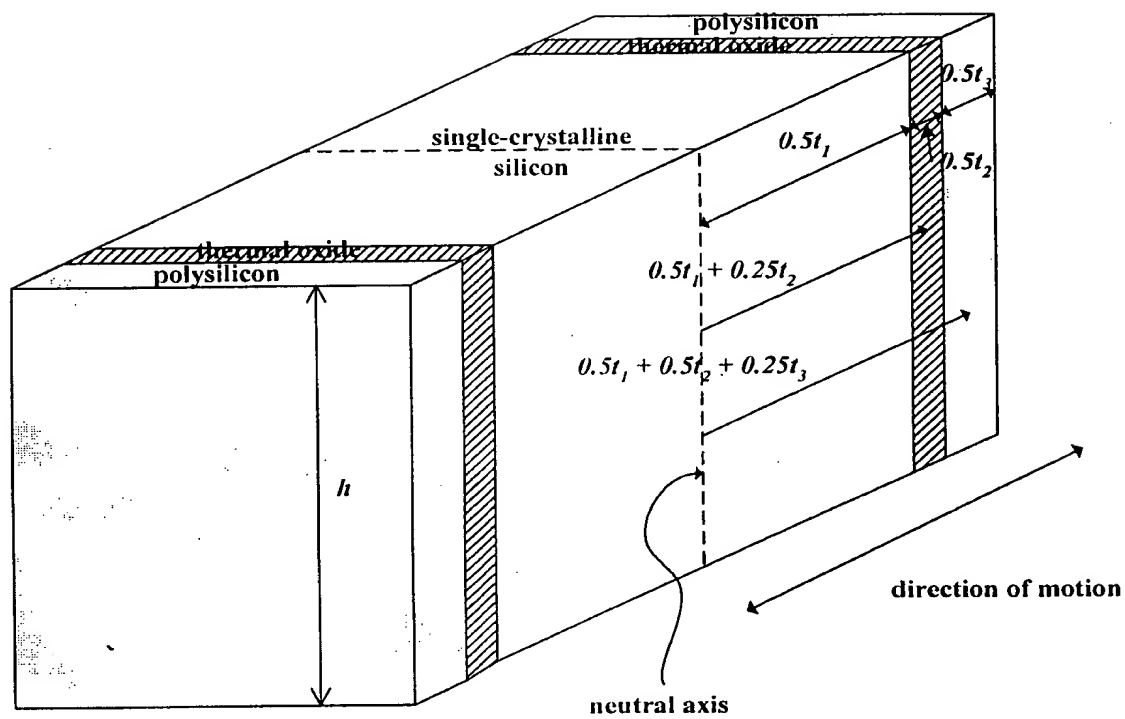


FIG. 9

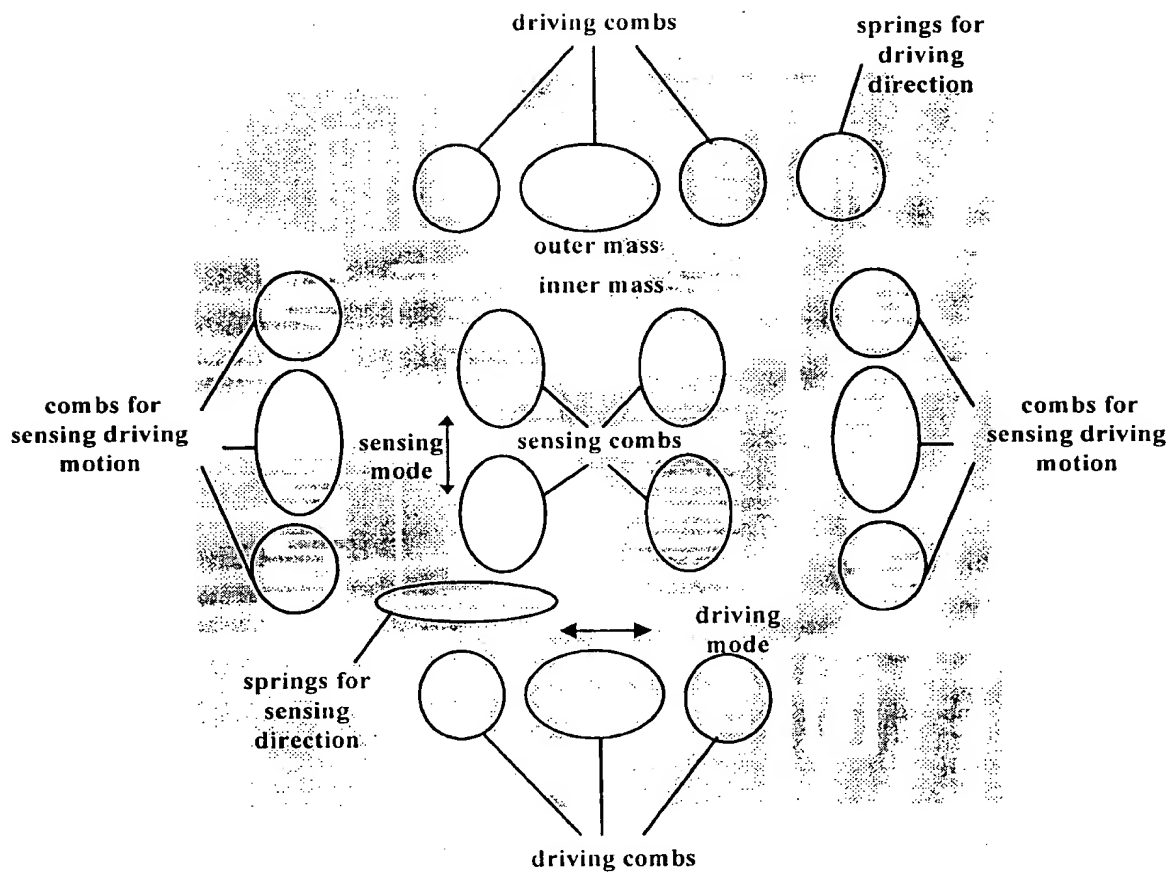


FIG. 10

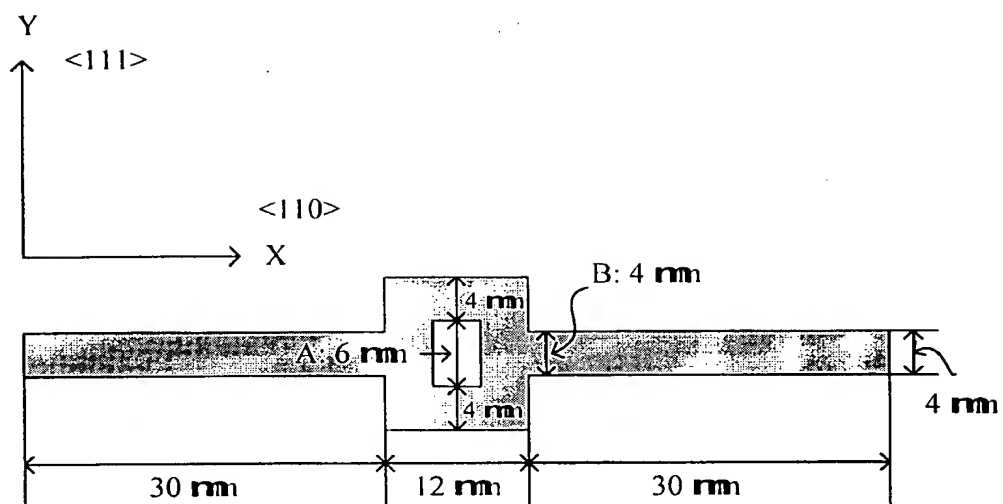


FIG. 11

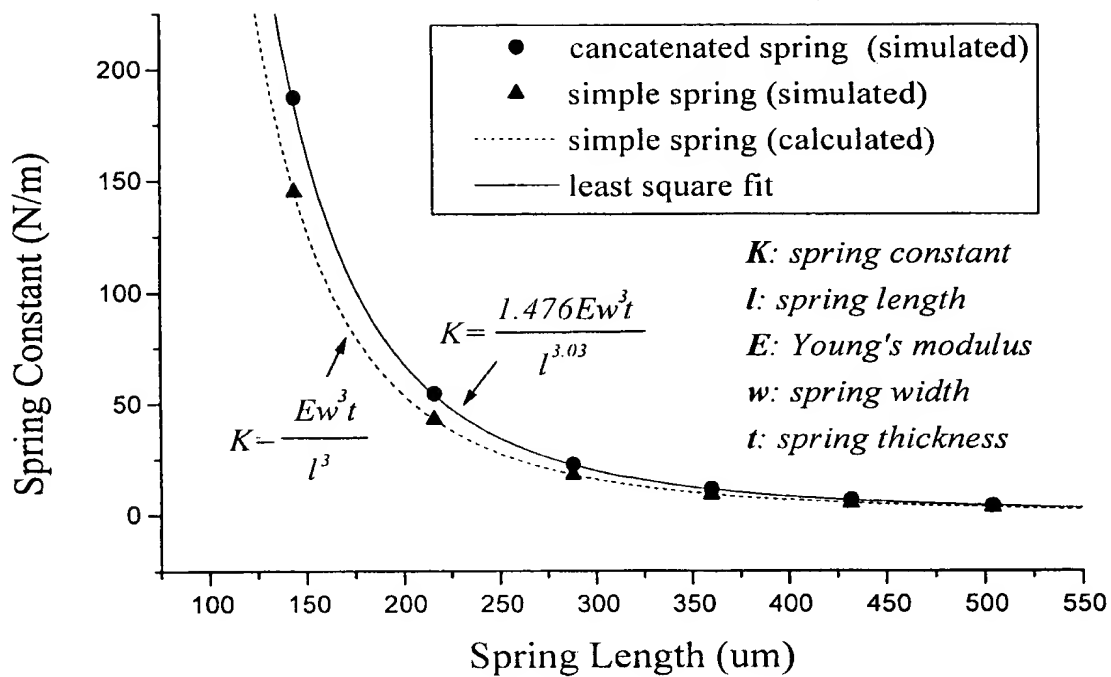
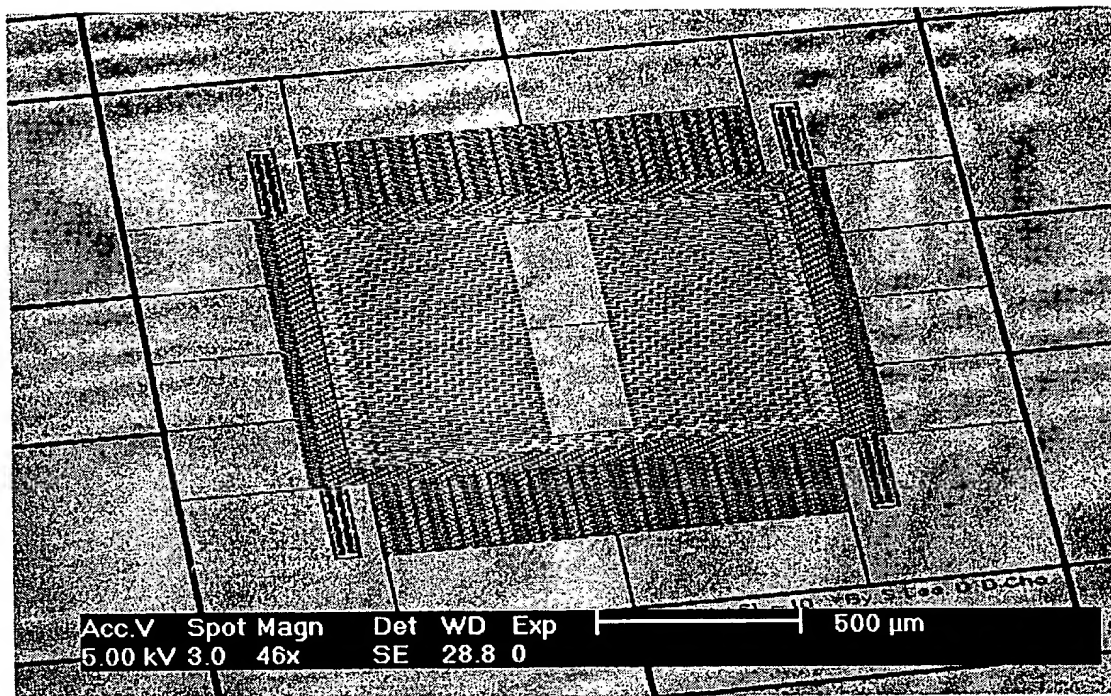
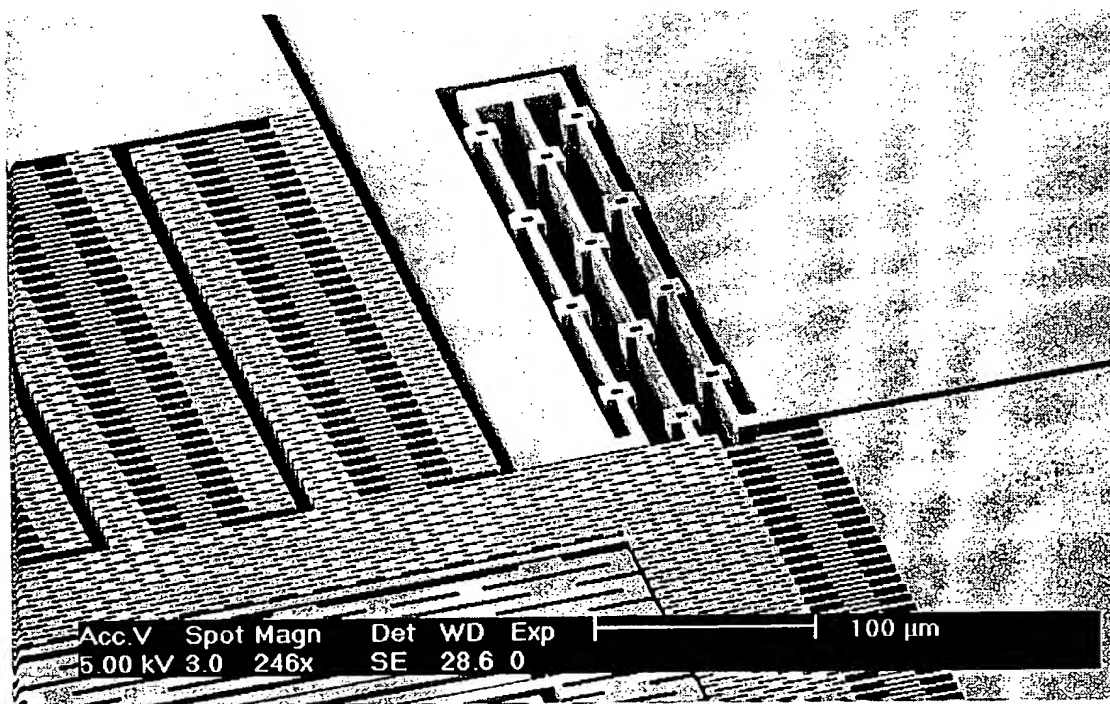


FIG. 12




(a)



(b)

Acc.V 5.00 kV Spot 3.0 Magn 983x Det SE WD 28.7 Exp 0

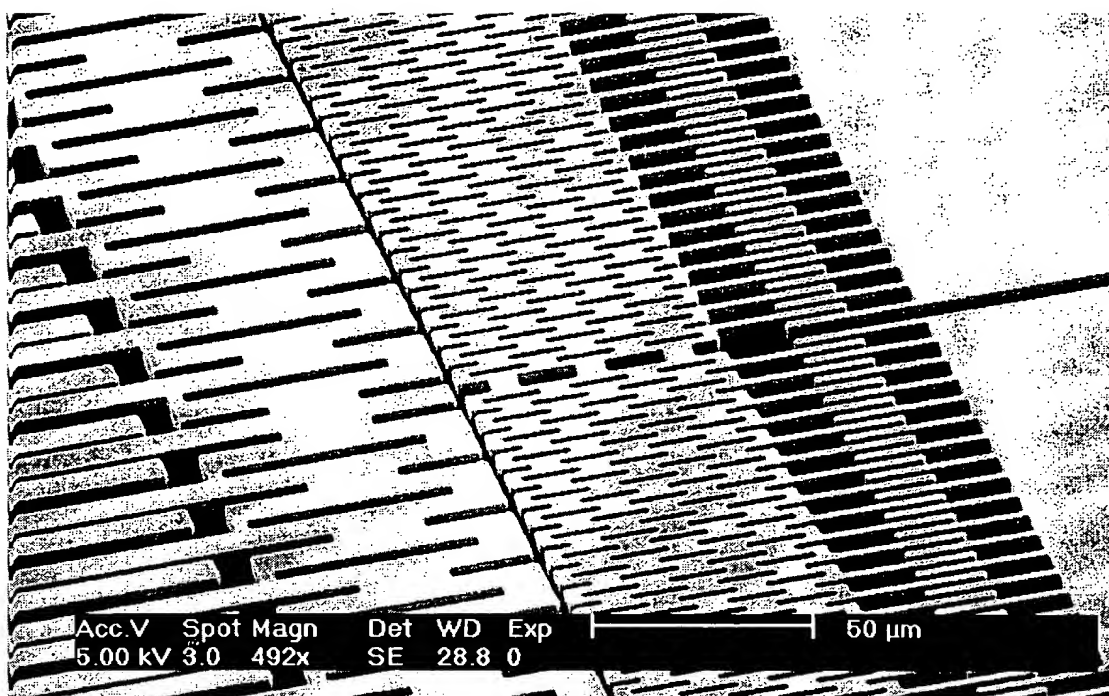
20 μm



Acc.V Spot Magn Det WD Exp | 20 μm
5.00 kV 3.0 983x SE 28.8 0

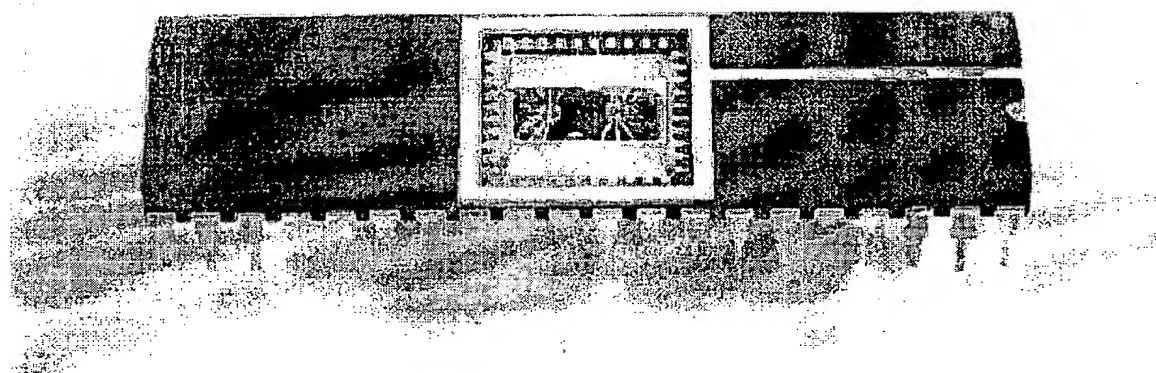
(d)

09903280.071101



(e)

FIG. 13



09903280-071101

FIG. 14

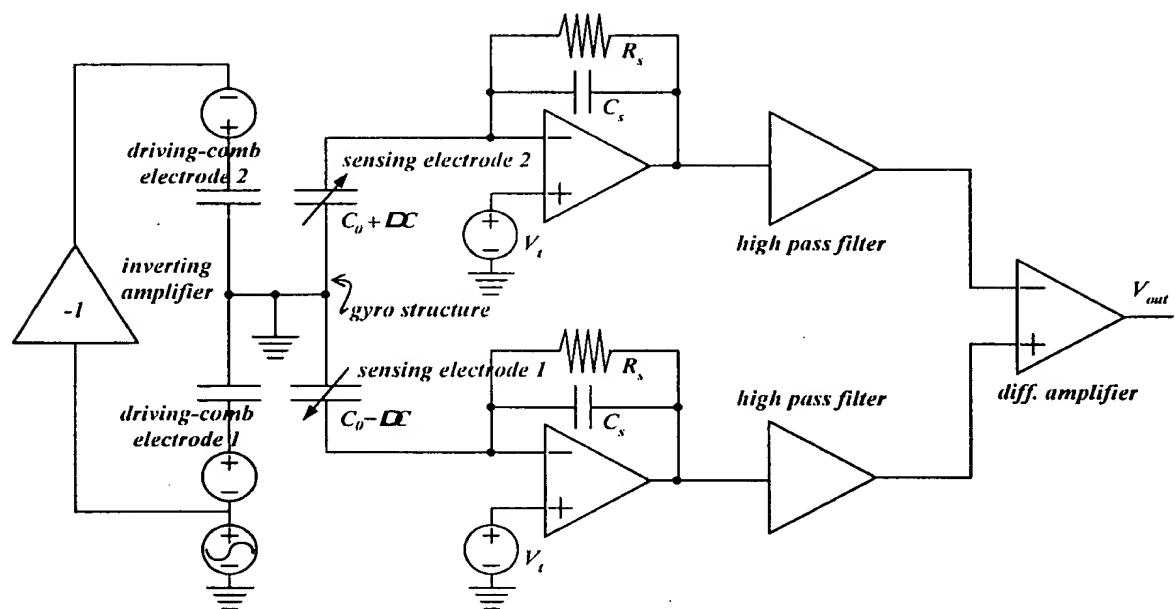


FIG. 15

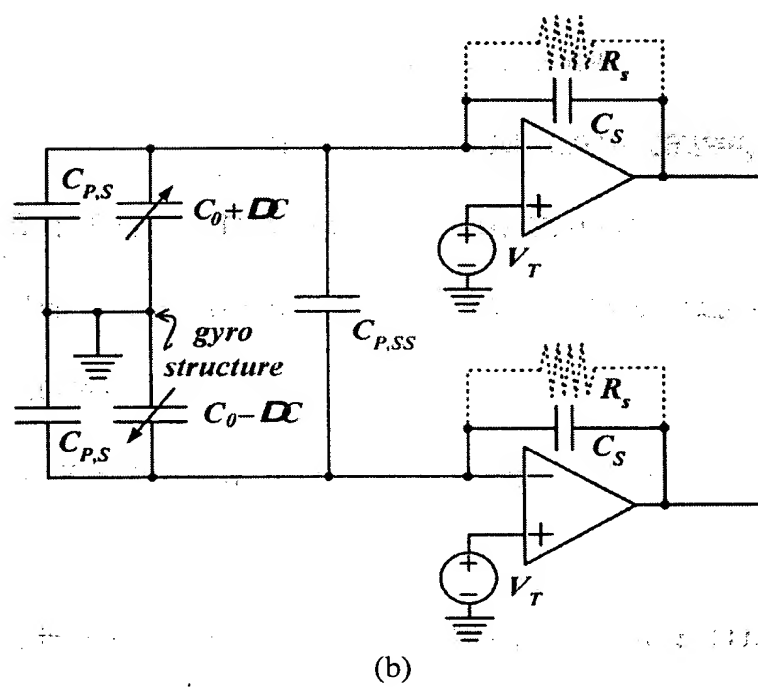
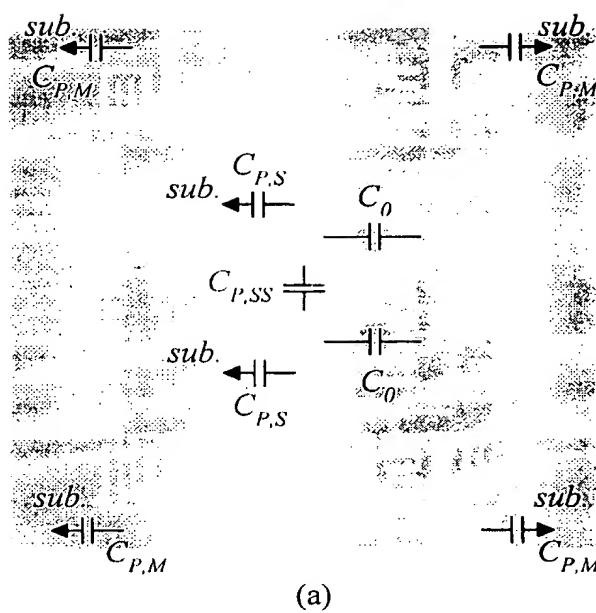
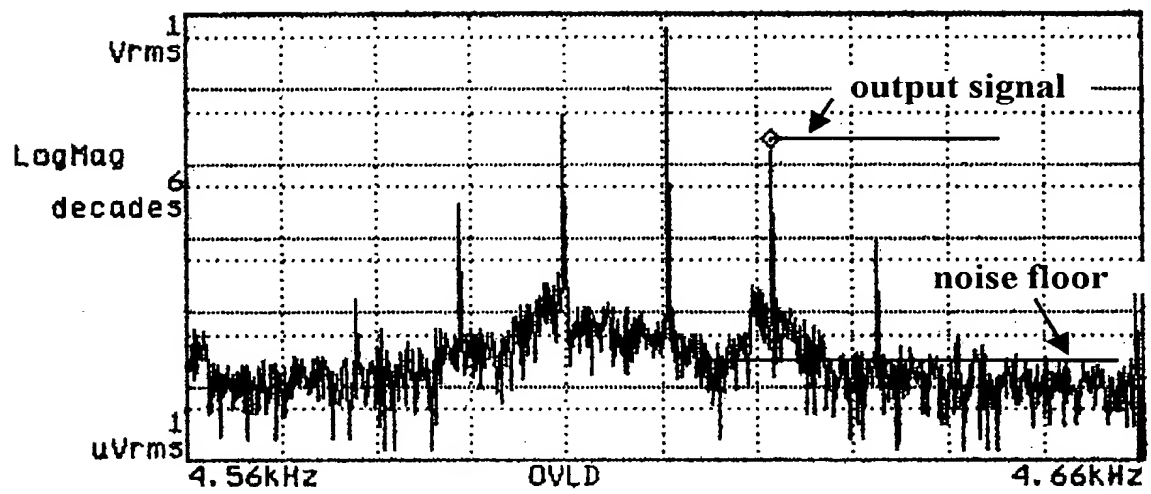


FIG. 16



(Y-axis corresponds to the root mean square voltage in Log-scale.)

0903280-071101

FIG. 17

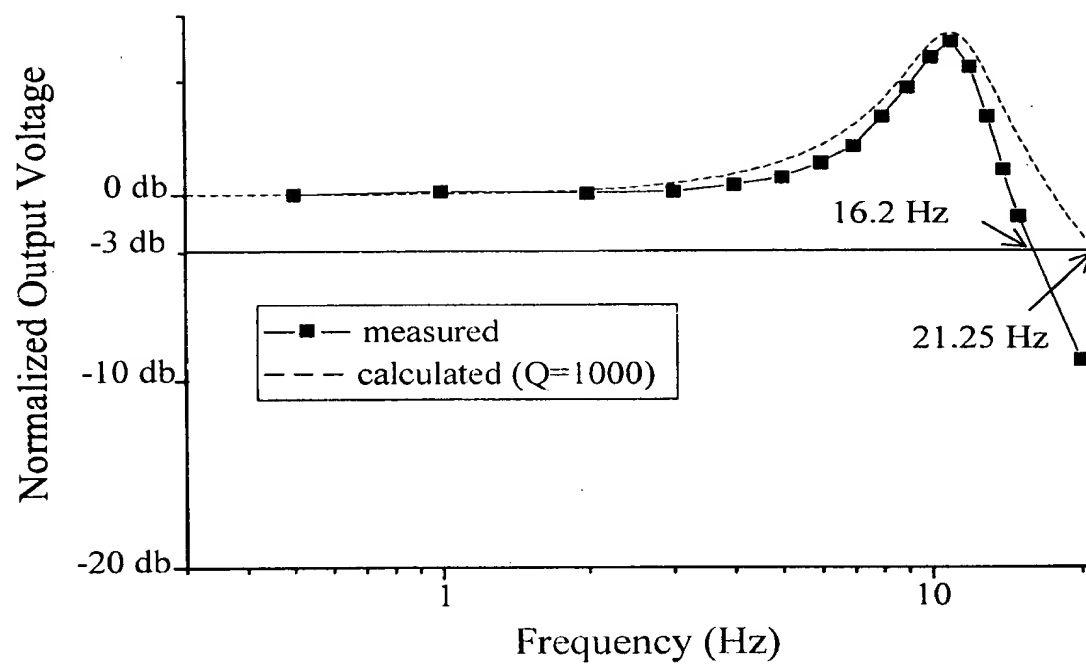
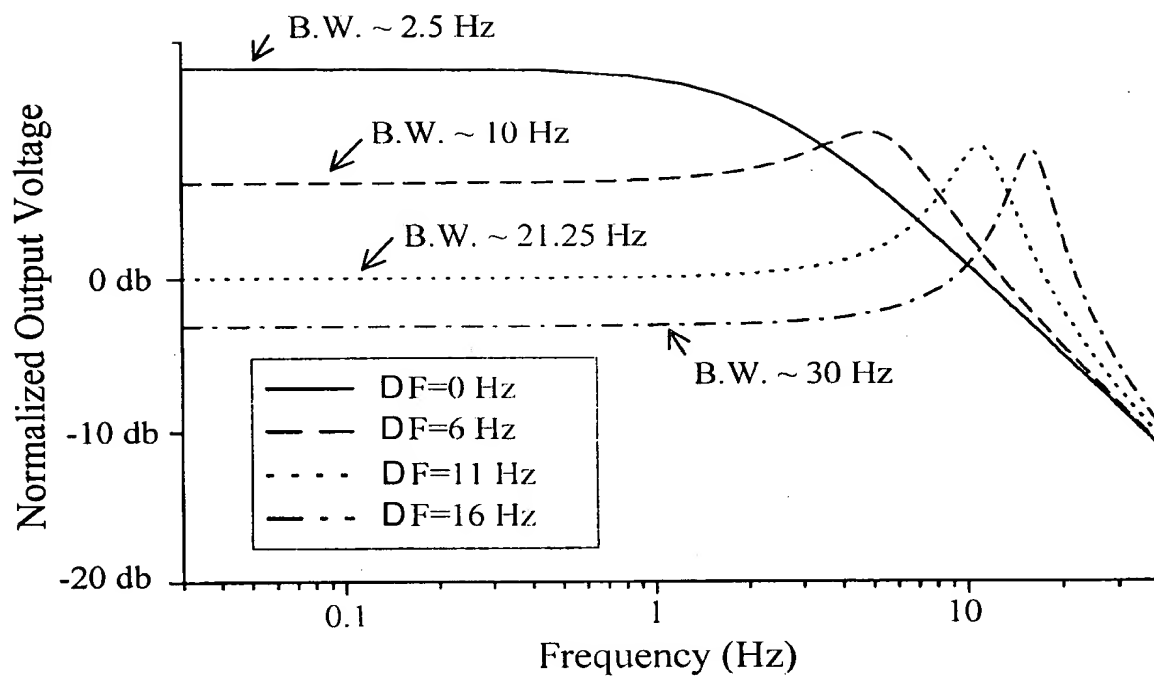


FIG. 18



TOPIC: 082E0660

FIG. 19

